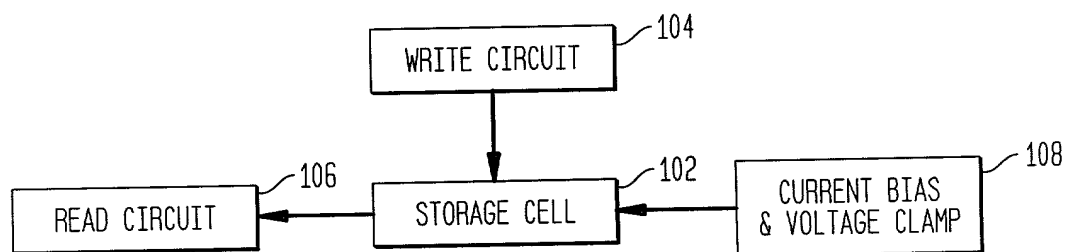
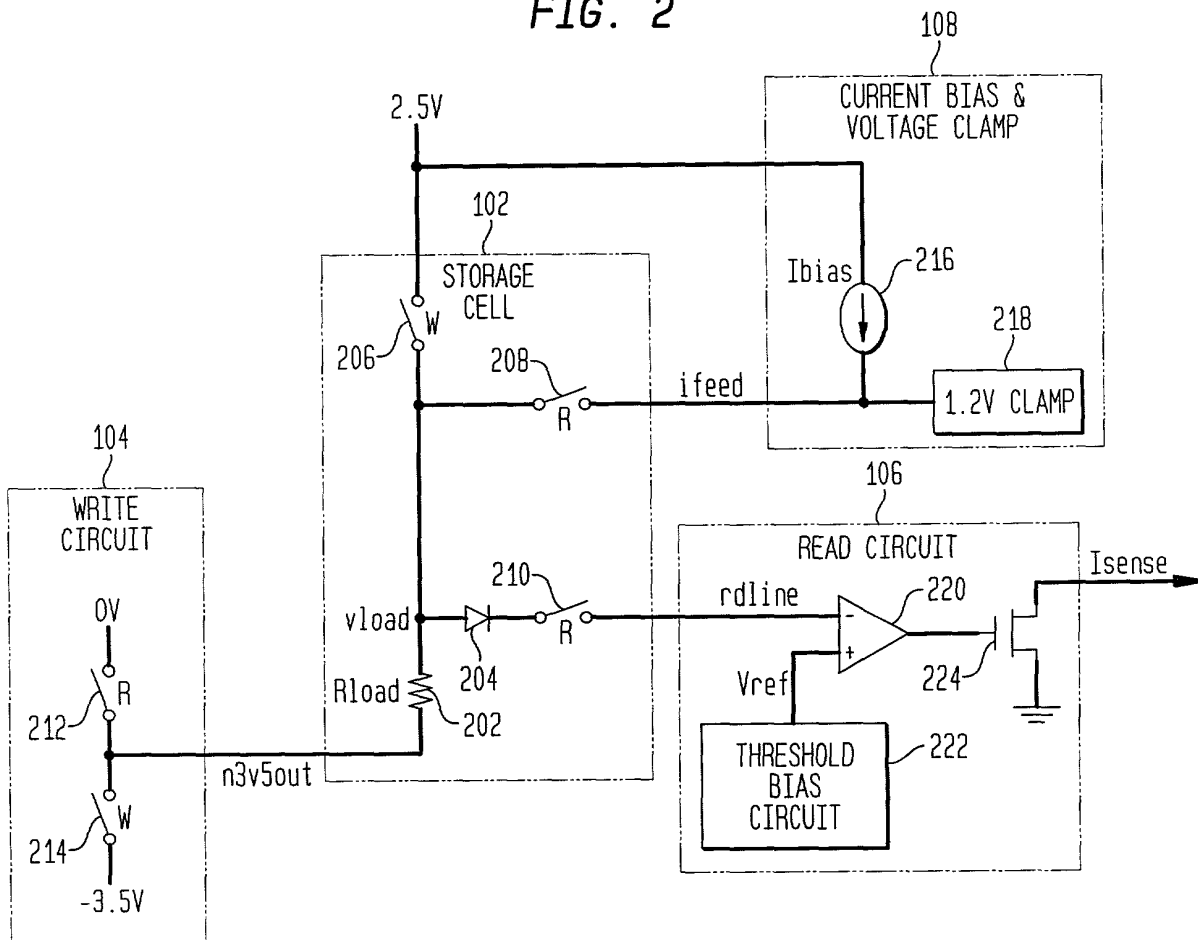


FIG. 1





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FIG. 3

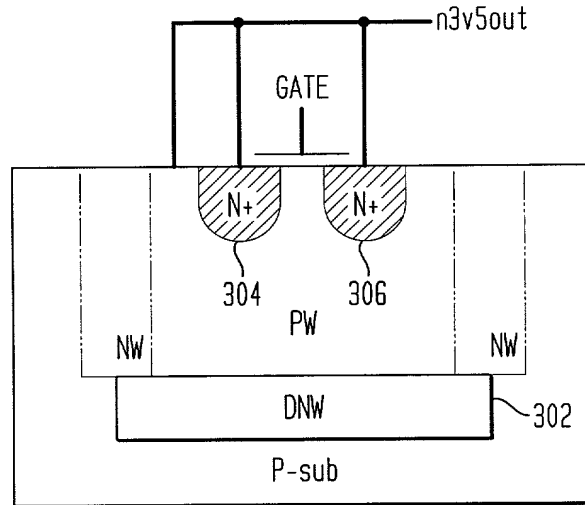
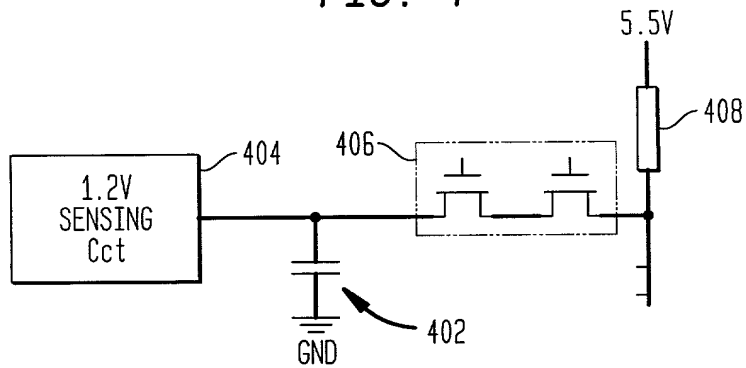


FIG. 4



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FIG. 5A

NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$ S/D FLOAT

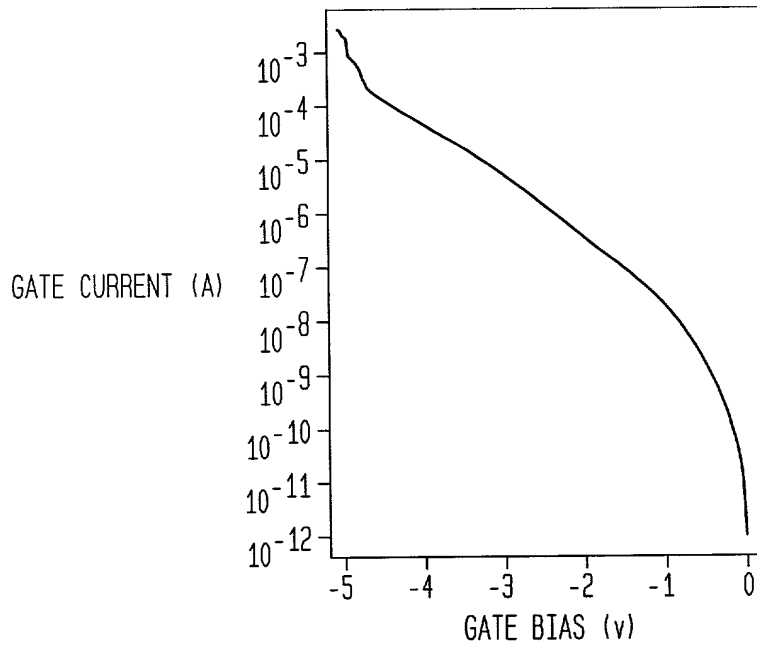
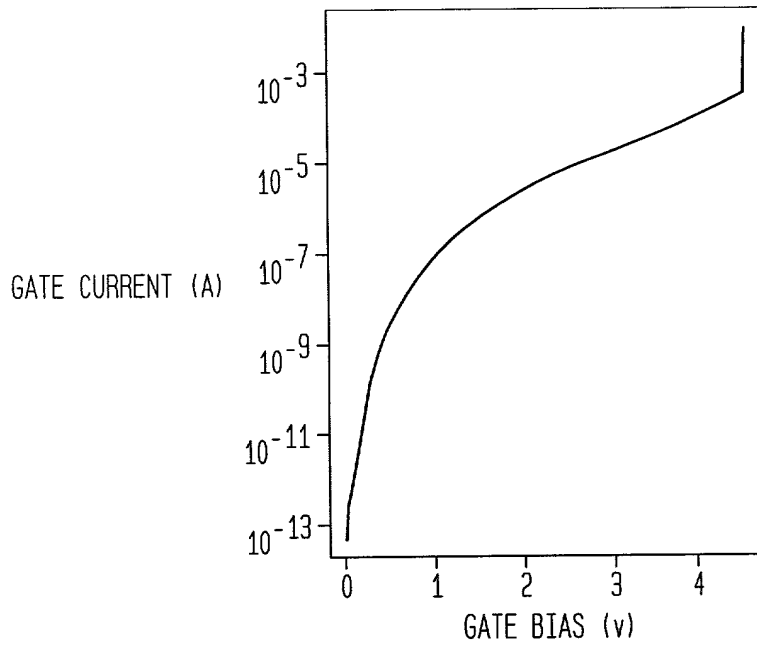


FIG. 5B

NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$

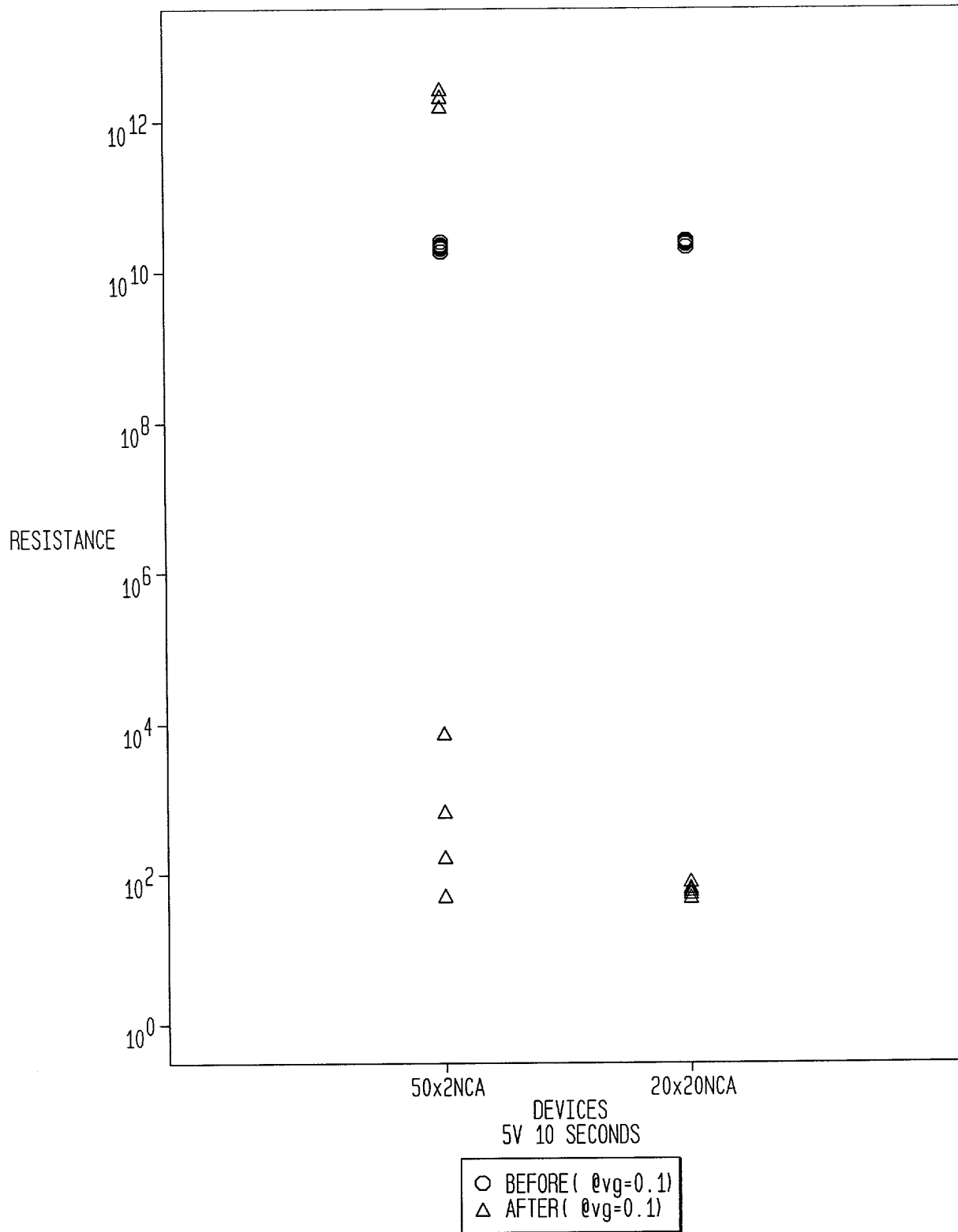


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 Title System and Method for One-Time Programmed Memory
 Through Direct-Tunneling Oxide Breakdown

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FIG. 6A

GATE OXIDE FUSE

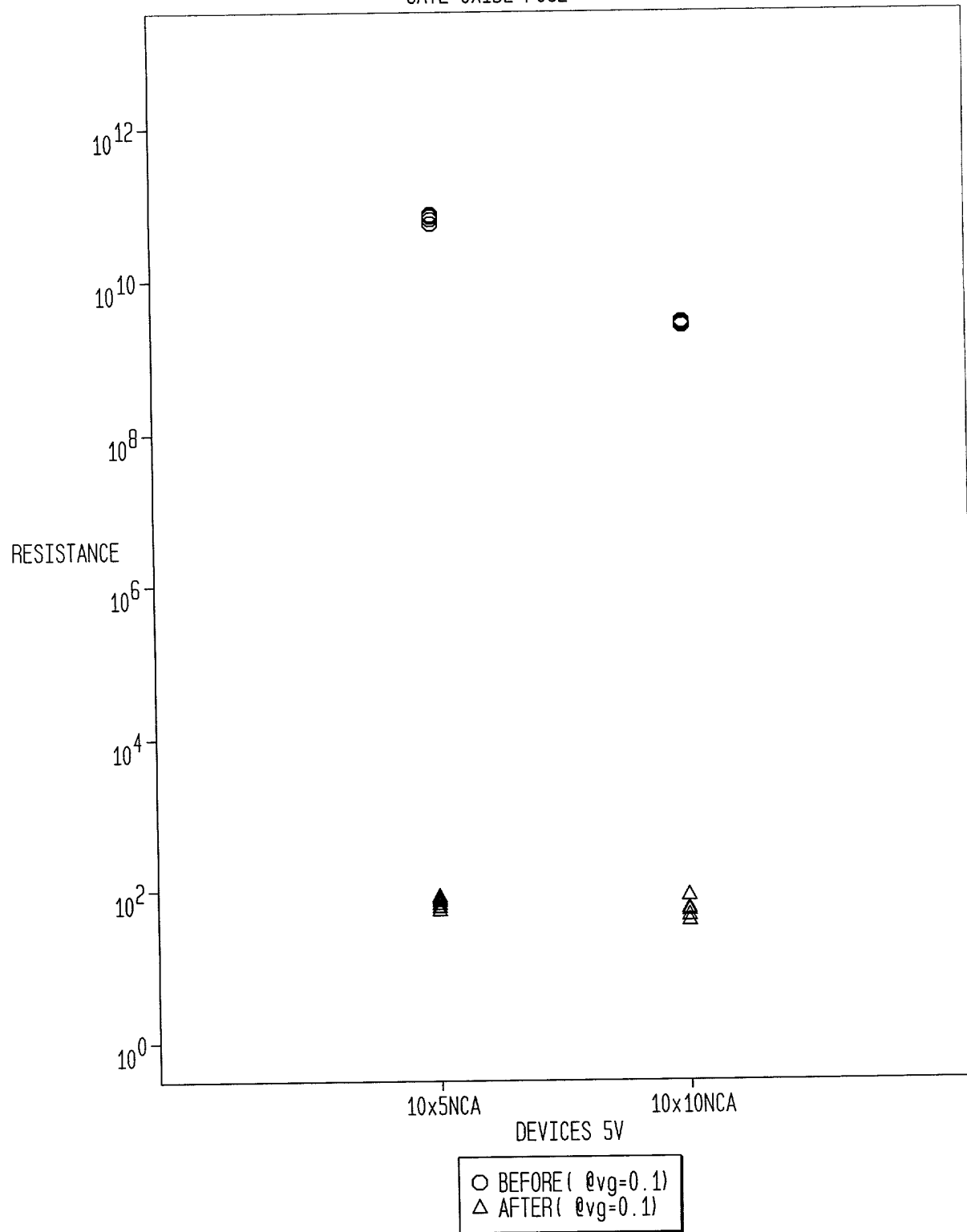


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Dkt. No. 1875 0220000, Batch No.:
Inventor(s) Chen *et al.*; Tel. 202/371-2600
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FIG. 6B

GATE OXIDE FUSE



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FIG. 7

